

100V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D $T_A = 25^\circ C$
-100V	350m Ω @ $V_{GS} = -10V$	-2.4
	450m Ω @ $V_{GS} = -6.0V$	-2.1

Description and Applications

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor control
- DC-DC Converters
- Power management functions
- Uninterrupted power supply

Features and Benefits

- Fast switching speed
- Low gate drive
- Low input capacitance
- **Qualified to AEC-Q101 Standards for High Reliability**

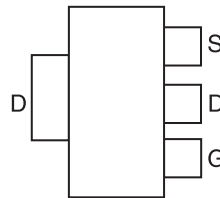
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.112 grams (approximate)

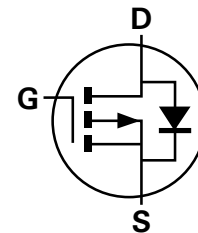
SOT223



Top View



Pin Out - Top View

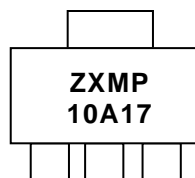


Equivalent Circuit

Ordering Information

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMP10A17GTA	See below	7	12	1,000

Marking Information



ZXMP = Product Type Marking Code, Line 1
10A17 = Product Type Marking Code, Line 2

Maximum Ratings @T_A = 25°C unless otherwise specified

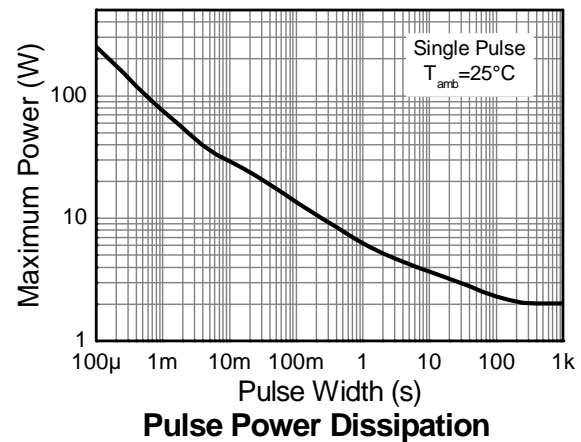
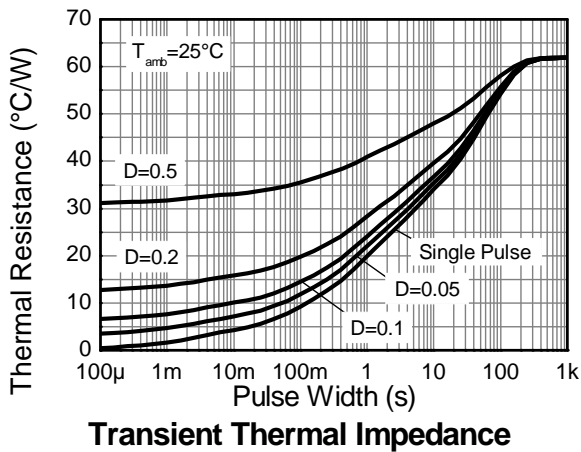
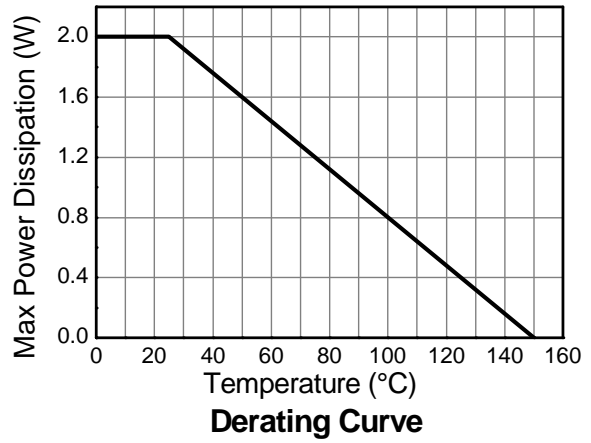
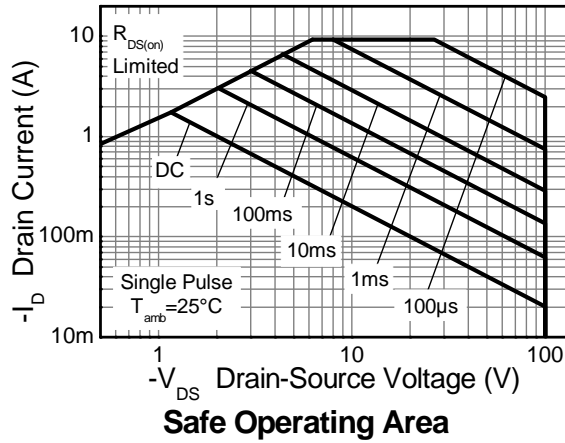
Characteristic			Symbol	Value	Unit
Drain-Source voltage			V _{DSS}	-100	V
Gate-Source voltage			V _{GS}	±20	V
Continuous Drain current	V _{GS} = 10V	(Note 2)	I _D	-2.4	A
		T _A = 70°C (Note 2)		-1.9	
		(Note 1)		-1.7	
Pulsed Drain current	V _{GS} = 10V	(Note 3)	I _{DM}	-9.4	A
Continuous Source current (Body diode)			I _S	-4.5	A
Pulsed Source current (Body diode)			I _{SM}	-9.4	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Power dissipation Linear derating factor		(Note 1)	P _D	2.0	W mW/°C
				16	
		(Note 2)		3.9	
Thermal Resistance, Junction to Ambient		(Note 1)	R _{θJA}	62.5	°C/W
		(Note 2)		32.0	
Thermal Resistance, Junction to Lead		(Note 4)	R _{θJL}	9.8	
Operating and storage temperature range			T _J , T _{STG}	-55 to 150	°C

- Notes:
1. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 2. Same as note (1), except the device is measured at t ≤ 10 sec.
 3. Same as note (1), except the device is pulsed with D= 0.02 and pulse width 300 μs. The pulse current is limited by the maximum junction temperature.
 4. Thermal resistance from junction to solder-point (at the end of the drain lead).

Thermal Characteristics

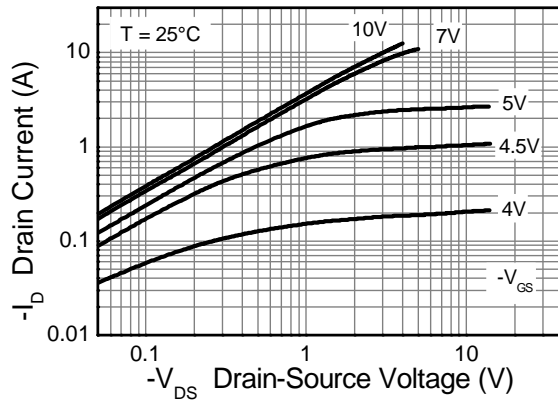


Electrical Characteristics @T_A = 25°C unless otherwise specified

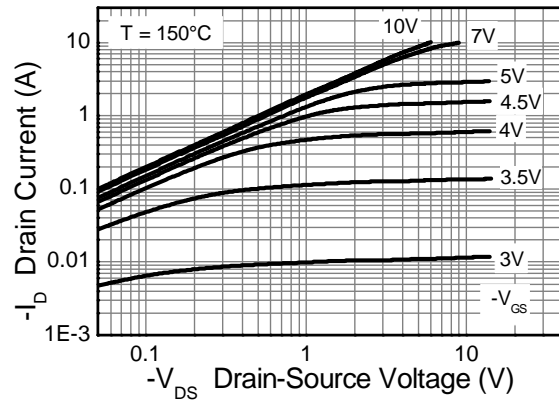
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	-100	—	—	V	I _D = -250μA, V _{GS} = 0V
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-0.5	μA	V _{DS} = -100V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	-2.0	—	-4.0	V	I _D = -250μA, V _{DS} = V _{GS}
Static Drain-Source On-Resistance (Note 5)	R _{DS(on)}	—	—	0.350	Ω	V _{GS} = -10V, I _D = -1.4A
				0.450		V _{GS} = -6V, I _D = -1.2A
Forward Transconductance (Notes 5 & 6)	g _{fs}	—	2.8	—	S	V _{DS} = -15V, I _D = -1.4A
Diode Forward Voltage (Note 5)	V _{SD}	—	-0.85	-0.95	V	I _S = -1.7A, V _{GS} = 0V
Reverse recovery time (Note 6)	t _{rr}	—	33	—	ns	I _S = -1.5A, di/dt = 100A/μs
Reverse recovery charge (Note 6)	Q _{rr}	—	48	—	nC	
DYNAMIC CHARACTERISTICS (Note 6)						
Input Capacitance	C _{iss}	—	424	—	pF	V _{DS} = -50V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	36.6	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	29.8	—	pF	
Total Gate Charge (Note 7)	Q _g	—	7.1	—	nC	V _{GS} = -6.0V
Total Gate Charge (Note 7)	Q _g	—	10.7	—	nC	V _{GS} = -10V V _{DS} = -50V I _D = -1.4A
Gate-Source Charge (Note 7)	Q _{gs}	—	1.7	—	nC	
Gate-Drain Charge (Note 7)	Q _{gd}	—	3.8	—	nC	
Turn-On Delay Time (Note 7)	t _{D(on)}	—	3.0	—	ns	V _{DD} = -50V, V _{GS} = -10V I _D = -1A, R _G = 6.0Ω
Turn-On Rise Time (Note 7)	t _r	—	3.5	—	ns	
Turn-Off Delay Time (Note 7)	t _{D(off)}	—	13.4	—	ns	
Turn-Off Fall Time (Note 7)	t _f	—	7.2	—	ns	

- Notes:
5. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
 6. For design aid only, not subject to production testing.
 7. Switching characteristics are independent of operating junction temperatures.

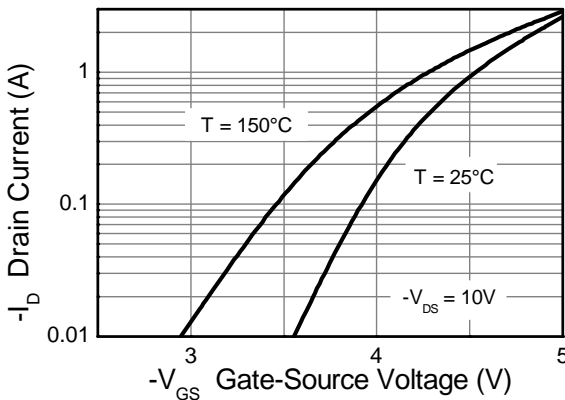
Typical Characteristics



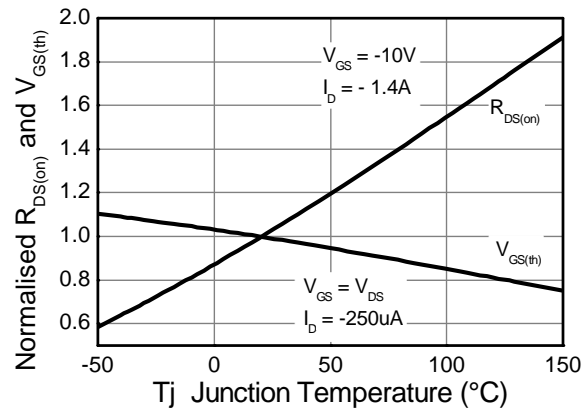
Output Characteristics



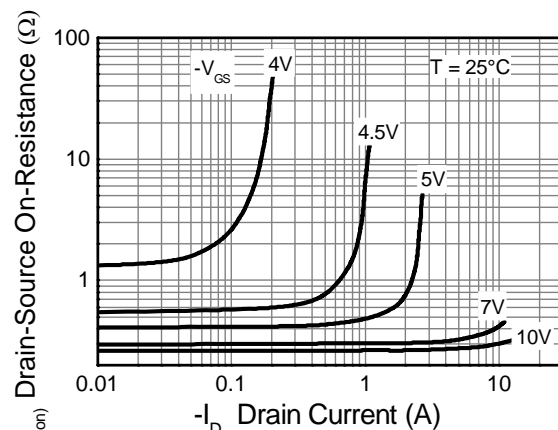
Output Characteristics



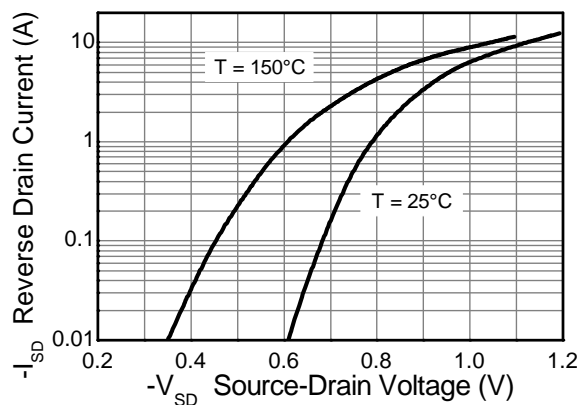
Typical Transfer Characteristics



Normalised Curves v Temperature

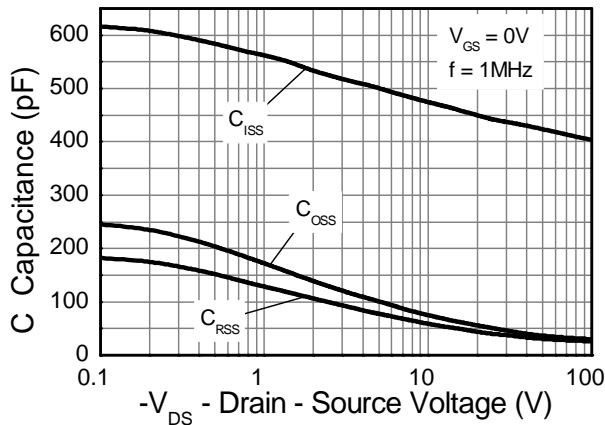


On-Resistance v Drain Current

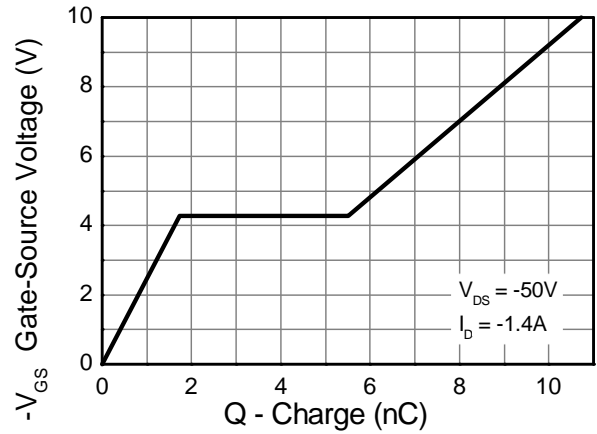


Source-Drain Diode Forward Voltage

Typical Characteristics - continued

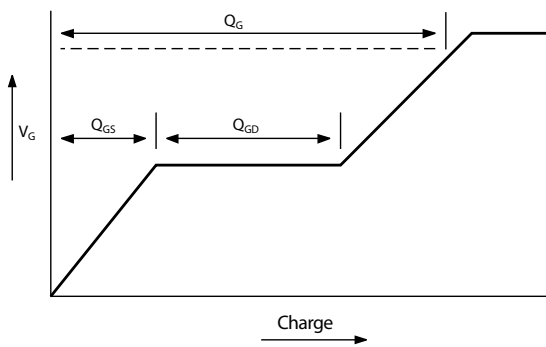


Capacitance v Drain-Source Voltage

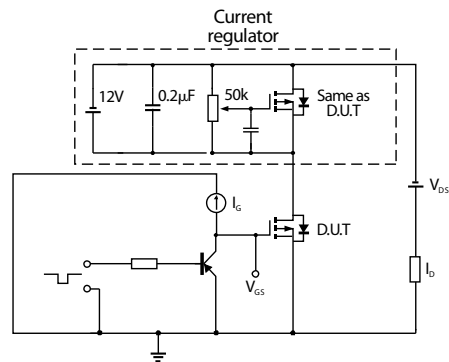


Gate-Source Voltage v Gate Charge

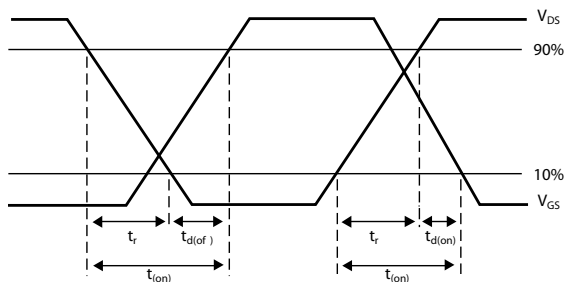
Test Circuits



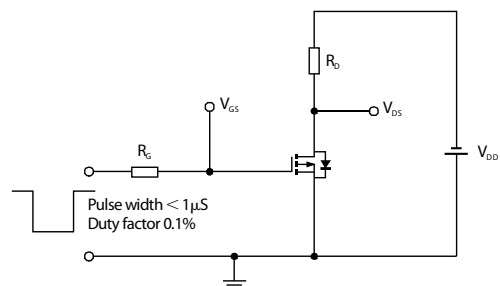
Basic gate charge waveform



Gate charge test circuit

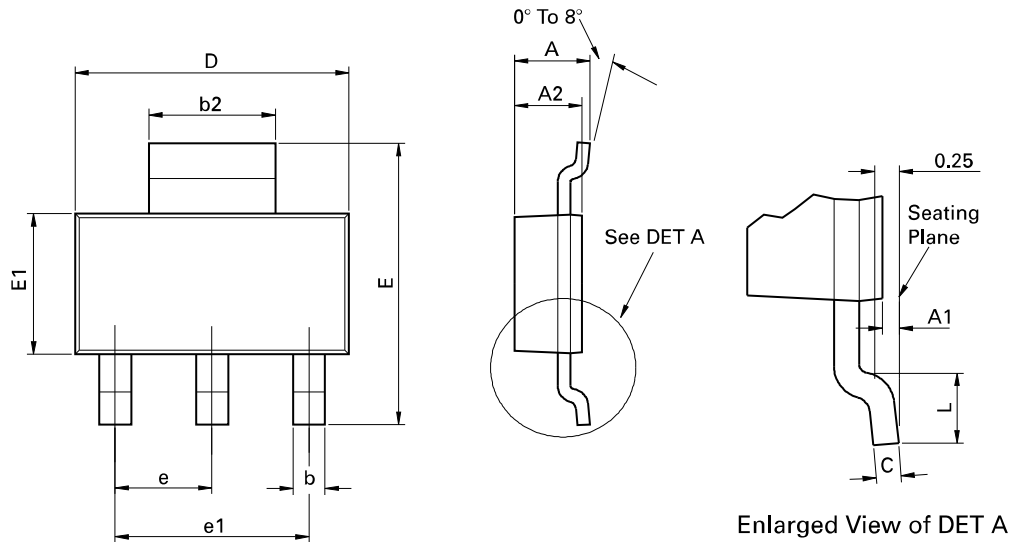


Switching time waveforms



Switching time test circuit

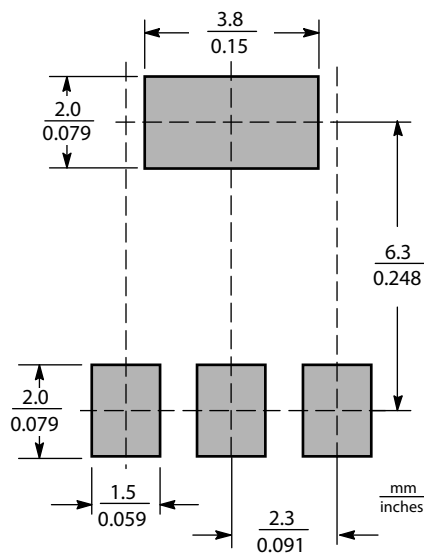
Package Outline Dimensions



Conforms to JEDEC TO-261 AA Issue B

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	-	1.80	-	0.071	D	6.30	6.70	0.248	0.264
A1	0.02	0.10	0.0008	0.004	e	2.30 BSC		0.0905 BSC	
A2	1.55	1.65	0.0610	0.0649	e1	4.60 BSC		0.181 BSC	
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
C	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-

Suggested Pad Layout



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